

1 S 129 [Japan]	Tos	Ge-Di	S, 50V, 0.1A, <240ns	31a	DO-7			AAY 49, AAZ 15, AAZ 17
1 S 130 [Japan]	Tos	Ge-Di	=1S129[Japan]: <340ns	31a	DO-7			AAY 49, AAZ 15, AAZ 17
1 S 130 [Texas]	Tix	Si-Di	Uni, 50V, 0.2A	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 131 [Japan]	Tos	Ref-Di	8...9.5V	=34a				
1 S 131 [Texas]	Tix	Si-Di	=1S130[Texas]: 100V	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 132 [Japan]	Tos	Ref-Di	8...9.5V	=34a				
1 S 132 [Texas]	Tix	Si-Di	=1S130[Texas]: 200V	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 133 [Japan]	Tos	Ref-Di	8...9.5V	=34a				
1 S 134 [Japan]	Tos	Z-Di	3.8...5.4V, 0.25W	31a	DO-7	Z-Diode 4.7V		BZX55/C4V7, BZX79/C4V7, ZPD4.7, 1N5230++
1 S 134 [Texas]	Tix	Si-Di	=1S130[Texas]: 400V	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 135 [Japan]	Tos	Z-Di	=1S134[Japan]: 5.2...6.2V	31a	DO-7	Z-Diode 5.6V	31a	BZX55/C5V6, BZX79/C5V6, ZPD5.6, 1N5232++
1 S 136 [Japan]	Tos	Z-Di	=1S134[Japan]: 6.0...7.1V	31a	DO-7	Z-Diode 6.8V	31a	BZX55/C6V8, BZX79/C6V8, ZPD6.8, 1N5235++
1 S 136 [Texas]	Tix	Si-Di	=1S130[Texas]: 600V	31a	DO-7	BA 159	31a	BA 158...159, BY 204/8, BY 207, ++
1 S 137 [Japan]	Tos	Z-Di	=1S134[Japan]: 6.9...8.1V	31a	DO-7	Z-Diode 7.5V	31a	BZX55/C7V5, BZX79/C7V5, ZPD7.5, 1N5236++
1 S 138 [Japan]	Tos	Z-Di	=1S134[Japan]: 7.9...9.1V	31a	DO-7	Z-Diode 8.2V	31a	BZX55/C8V2, BZX79/C8V2, ZPD8.2, 1N5237++
1 S 138 [Texas]	Tix	Si-Di	=1S130[Texas]: 800V	31a	DO-7	BA 159	31a	BA 159, BY 204/8, BY 208/800, ++
1 S 139 [Japan]	Tos	Z-Di	=1S134[Japan]: 8.9...10.1V	31a	DO-7	Z-Diode 9.1V	31a	BZX55/C9V1, BZX79/C9V1, ZPD9.1, 1N5239++
1 S 140 [Japan]	Tos	Z-Di	=1S134[Japan]: 9.9...12.2V	31a	DO-7	Z-Diode 11V	31a	BZX55/C11, BZX79/C11, ZPD11, 1N5241++
1 S 140 [Texas]	Tix	Si-Di	Rr, 50V, 0.3A	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 141 [Japan]	Tos	Z-Di	=1S134[Japan]: 11.8...13.9V	31a	DO-7	Z-Diode 13V	31a	BZX55/C13, BZX79/C13, ZPD13, 1N5243++
1 S 141 [Texas]	Tix	Si-Di	=1S140[Texas]: 100V	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 142 [Japan]	Tos	Z-Di	=1S134[Japan]: 13.3...15.5V	31a	DO-7	Z-Diode 15V	31a	BZX55/C15, BZX79/C15, ZPD15, 1N5245++
1 S 142 [Texas]	Tix	Si-Di	=1S140[Texas]: 200V	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 143 [Japan]	Tos	Z-Di	=1S134[Japan]: 14.7...17.3V	31a	DO-7	Z-Diode 16V	31a	BZX55/C16, BZX79/C16, ZPD16, 1N5246++
1 S 144 [Japan]	Tos	Si-Di	Meßwerkschutz/Meter Protection	31a	DO-7			
1 S 144 [Texas]	Tix	Si-Di	=1S140[Texas]: 400V	31a	DO-7	BA 159	31a	BA 157...159, BY 204/4, BY 206...207, ++
1 S 145 [Japan]	Tos	C-Di	FM/VHF AFC	31a	DO-7			BA 124...125, BB 119, 1S2790, 1S1V50, ++
1 S 146 [Japan]	Fui	Si-Di	Rr, Uni, 100V, 0.6A, Uf<1.2V(0.6A)	31a	DO-27			BY 126...127, BY 133...135, 1N4002...07, ++
1 S 147 [Japan]		Si-Di	=1S146[Japan]: 200V	31a	DO-27			BY 126...127, BY 133...134, 1N4003...07, ++
1 S 148 [Japan]		Si-Di	=1S146[Japan]: 300V	31a	DO-27			BY 126...127, BY 133...134, 1N4004...07, ++
1 S 149 [Japan]		Si-Di	=1S146[Japan]: 400V	31a	DO-27			BY 126...127, BY 133...134, 1N4004...07, ++
1 S 150 [Japan]		Si-Di	=1S146[Japan]: 500V	31a	DO-27			BY 126...127, BY 133...134, 1N4005...07, ++
1 S 151	Nec	Si-Di	P Rr, 100V, 1.5A, Uf<1.3V(1A)	32a	DO-4			BYX 38/300, BYX 39/600
1 S 152		Si-Di	=1S151: 200V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 153		Si-Di	=1S151: 300V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 154		Si-Di	=1S151: 400V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 155		Si-Di	=1S151: 500V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 156		Si-Di	=1S151: 600V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 157	Nec	Si-Di	P Rr, 100V, 1A, Uf<1.3V(1A)	32a	DO-4			BYX 38/300, BYX 39/600
1 S 158		Si-Di	=1S157: 200V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 159		Si-Di	=1S157: 300V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 160	Nec	Si-Di	P Rr, 50V, 10A(Tc=120°), Uf<1.6V(50A)	32a	DO-4			BYX 42/300, BYX 98/300
1 S 161		Si-Di	=1S160: 100V	32a	DO-4			BYX 42/300, BYX 98/300
1 S 162		Si-Di	=1S160: 200V	32a	DO-4			BYX 42/300, BYX 98/300
1 S 163		Si-Di	=1S160: 300V	32a	DO-4			BYX 42/300, BYX 98/300
1 S 164		Si-Di	=1S160: 400V	32a	DO-4			BYX 42/300, BYX 98/600
1 S 165		Si-Di	=1S160: 500V	32a	DO-4			BYX 42/600, BYX 98/600
1 S 166		Si-Di	=1S160: 600V	32a	DO-4			BYX 42/600, BYX 98/600
1 S 167	Nec	Si-Di	P Rr, 100V, 5A(Tc=120°), Uf<1.9V(50A)	32a	DO-4			BYX 38/300, BYX 39/600
1 S 168		Si-Di	=1S167: 200V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 169		Si-Di	=1S167: 300V	32a	DO-4			BYX 38/300, BYX 39/600
1 S 170	Nec	Si-Di	P Rr, 50V, 20A(Tc=120°), Uf<1.6V(100A)	32a	DO-5			1N4525...30
1 S 171		Si-Di	=1S170: 100V	32a	DO-5			1N4525...30
1 S 172		Si-Di	=1S170: 200V	32a	DO-5			1N4525...30
1 S 173		Si-Di	=1S170: 300V	32a	DO-5			1N4526...30
1 S 174		Si-Di	=1S170: 400V	32a	DO-5			1N4526...30
1 S 175		Si-Di	=1S170: 500V	32a	DO-5			1N4527...30
1 S 176		Si-Di	=1S170: 600V	32a	DO-5			1N4527...30
1 S 177	Nec	Si-Di	P Rr, 100V, 15A(Tc=120°), Uf<1.8V(100A)	32a	DO-5			1N4525...30
1 S 178		Si-Di	=1S177: 200V	32a	DO-5			1N4525...30
1 S 179		Si-Di	=1S177: 300V	32a	DO-5			1N4526...30
1 S 180	Tos	Si-Di	Dem, Uni, 70V, 0.1A	31a	DO-7	1N4148	31a	BA 147/100, BA 188...190, BAY 19...21, ++
1 S 181		Si-Di	=1S180: 120V	31a	DO-7	BA 159	31a	BA 147/150, BA 189...190, BAY 20...21, ++
1 S 182		Si-Di	=1S180: 220V	31a	DO-7			BA 147/230, BAY 21, BAY 46, BAY 88, ++
1 S 183		Si-Di	=1S180: 320V	31a	DO-7			BA 147/300, BAY 21, BAY 46, BAY 88, ++
1 S 184	Tos	Si-Di	Dem, S, 15V, 0.04A	31a	DO-7			BA 281
1 S 185	Tos	Si-Di	Dem, S, 15V, 0.04A	31a	DO-7			BA 281
1 S 186	Say	Ge-Di	Uni, 75V, 30mA	31a	DO-7			AA 117...118, AA 132...133
1 S 187(S)	Say	Ge-Di	Dem, 40V, 50mA	31a	DO-7			AA 113, AA 119, 1N34, 1N54, 1N60
1 S 188(AM,FM,G)	Say	Ge-Di	Dem, 25...40V, 50mA	31a	DO-7	AA 138	31a	AA 113, AA 119, 1N34, 1N54, 1N60, ++
1 S 189	Say	Ge-Di	Dem, 50V, 40mA	31a	DO-7			AA 113, AA 119, 1N34, 1N54, 1N60
1 S 190	Njr	Z-Di	4.4...5.6V, 0.4W	31a	DO-7			BZX55... BZX79/..., ZPD..., 1N5231...50, ++
1 S 191		Z-Di	=1S190: 5.4...6.6V	31a	DO-7			
1 S 192		Z-Di	=1S190: 6.4...7.6V	31a	DO-7			
1 S 193		Z-Di	=1S190: 7.4...8.6V	31a	DO-7			
1 S 194		Z-Di	=1S190: 8.4...9.6V	31a	DO-7			
1 S 195		Z-Di	=1S190: 9.4...10.6V	31a	DO-7			
1 S 196		Z-Di	=1S190: 10.4...11.6V	31a	DO-7			
1 S 197		Z-Di	=1S190: 11.4...12.6V	31a	DO-7			
1 S 198		Z-Di	=1S190: 12.4...16.1V	31a	DO-7			
1 S 199		Z-Di	=1S190: 15.9...20V	31a	DO-7			
1 S 200	Njr	Ge-Di	Dem, 35V, 25mA	31a	DO-7			AA 112...114, AA 119, 1N34, 1N54, 1N60, ++
1 S 201	Njr	Ge-Di	20V	2	TO-2			-
1 S 202	Njr	Ge-Di	20V	2	TO-1			-
1 S 203	Njr	Ge-Di	20V	2	TO-1			-
1 S 204	Njr	Si-Di	Rr, Uni, 250V, 0.1A, Uf<1.2V(0.1A)	31a	DO-7			BA 157...159, BA 199/250, BAY 88...90, ++
1 S 205		Si-Di	=1S204: 350V	31a	DO-7			BA 157...159, BA 199/350, BAY 88...90, ++
1 S 206		Si-Di	=1S204: 450V	31a	DO-7			BA 158...159, BA 199/450, BAY 89...90, ++
1 S 207		Si-Di	=1S204: 550V	31a	DO-7			BA 158...159, BA 199/550, BAY 89...90, ++
1 S 208	Njr	Si-Di	Rr, Uni, 250V, 0.4A, Uf<1.2V(0.5A)	34	DO-1			BY 126...127, BY 133...134, 1N4004...07, ++
1 S 209		Si-Di	=1S208: 450V	34	DO-1			BY 126...127, BY 133...134, 1N4005...07, ++
1 S 210		Si-Di	=1S208: 650V	34	DO-1			BY 127, BY 133, BY 227, 1N4006...07, ++
1 S 211		Si-Di	=1S208: 850V	34	DO-1			BY 127, BY 133, BY 227, 1N4007, ++